

### ● General Description

The AGM30P08AP combines advanced trench MOSFET technology with a low resistance package to provide extremely low  $R_{DS(ON)}$ . This device is ideal for load switch and battery protection applications.

### ● Features

- Advance high cell density Trench technology
- Low  $R_{DS(ON)}$  to minimize conductive loss
- Low Gate Charge for fast switching
- Low Thermal resistance
- 100% Avalanche tested
- 100% DVDS tested

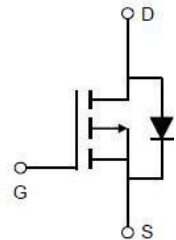
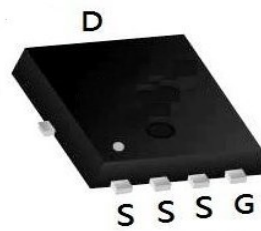
### ● Application

- MB/VGA Vcore
- SMPS 2<sup>nd</sup> Synchronous Rectifier
- POL application
- BLDC Motor driver

### Product Summary

BVDSS	RDSON	ID
-30V	7.2mΩ	-60A

### PDFN3.3\*3.3 Pin Configuration



### Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
AGM30P08AP	AGM30P08AP	PDFN3.3*3.3	330mm	12mm	5000

**Table 1. Absolute Maximum Ratings (TA=25°C)**

Symbol	Parameter	Value	Unit
VDS	Drain-Source Voltage (VGS=0V)	-30	V
VGS	Gate-Source Voltage (VDS=0V)	±20	V
ID	Drain Current-Continuous(Tc=25°C) <b>(Note 1)</b>	-60	A
	Drain Current-Continuous(Tc=100°C)	-39	A
IDM (pluse)	Drain Current-Continuous@ Current-Pulsed <b>(Note 2)</b>	-240	A
PD	Maximum Power Dissipation(Tc=25°C)	50	w
	Maximum Power Dissipation(Tc=100°C)	20	w
EAS	Avalanche energy <b>(Note 3)</b>	196	mJ
TJ,TSTG	Operating Junction and Storage Temperature Range	-55 To 150	°C

**Table 2. Thermal Characteristic**

Symbol	Parameter	Typ	Max	Unit
RθJA	Thermal Resistance Junction-ambient (Steady State) <sup>1</sup>	---	50	°C/W
RθJC	Thermal Resistance Junction-Case <sup>1</sup>	---	2.5	°C/W

**Table 3. Electrical Characteristics (T<sub>J</sub>=25°C unless otherwise noted)**

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>On/Off States</b>						
BVDSS	Drain-Source Breakdown Voltage	VGS=0V ID=250μA	-30	--	--	V
IDSS	Zero Gate Voltage Drain Current	VDS=-30V,VGS=0V	--	--	-1.0	μA
IGSS	Gate-Body Leakage Current	VGS=±20V,VDS=0V	--	--	±100	nA
VGS(th)	Gate Threshold Voltage	VDS=VGS,ID=-250μA	-1.2	-1.6	-2.5	V
gFS	Forward Transconductance	VDS=-10V,ID=-10A	--	17	--	S
RDS(on)	Drain-Source On-State Resistance	VGS=-10V, ID=-15A	--	7.2	8.5	mΩ
		VGS=-4.5V, ID=-10A	--	11.5	13	mΩ
<b>Dynamic Characteristics</b>						
Ciss	Input Capacitance	VDS=-30V,VGS=0V F=1MHZ	--	2497	--	pF
Coss	Output Capacitance		--	240	--	pF
Crss	Reverse Transfer Capacitance		--	230	--	pF
Rg	Gate resistance	VGS=0V, VDS=0V,f=1.0MHz	--	--	--	Ω
<b>Switching Times</b>						
td(on)	Turn-on Delay Time	VGS=-10V,VDS=-10V, ID=-30A,RGEN=3Ω	--	14	--	nS
tr	Turn-on Rise Time		--	20	--	nS
td(off)	Turn-Off Delay Time		--	56	--	nS
tf	Turn-Off Fall Time		--	48	--	nS
Qg	Total Gate Charge	VGS=-10V, VDS=-15V, ID=-20A	--	32	--	nC
Qgs	Gate-Source Charge		--	6.6	--	nC
Qgd	Gate-Drain Charge		--	8.0	--	nC
<b>Source-Drain Diode Characteristics</b>						
ISD	Source-Drain Current(Body Diode)		--	--	-60	A
VSD	Forward on Voltage	VGS=0V,IS=-1A	--	--	-1.2	V
trr	Reverse Recovery Time	IF=-15A , dI/dt=100A/μs , TJ=25°C	--	--	--	ns
Qrr	Reverse Recovery Charge		--	--	--	nc

Notes 1.The maximum current rating is package limited.

Notes 2.Repetitive Rating: Pulse width limited by maximum junction temperature

Notes 3.EAS condition: T<sub>J</sub>=25°C

### P- Channel Typical Characteristics

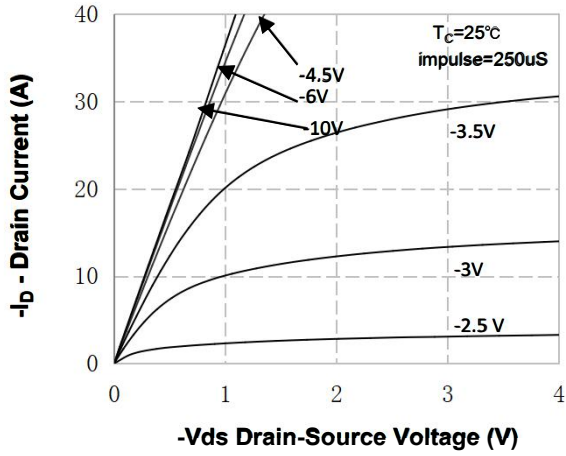


Figure 1. On-Region Characteristics

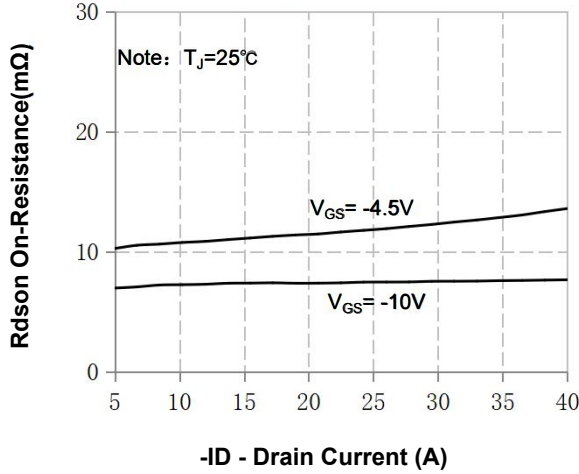


Figure 3. On-Resistance Variation vs Drain Current and Gate Voltage

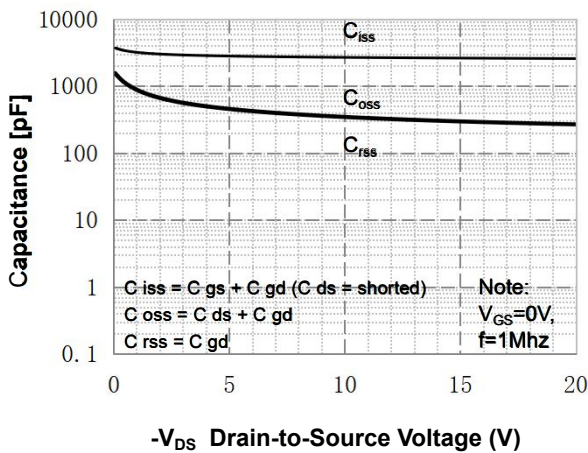


Figure 5. Capacitance Characteristics

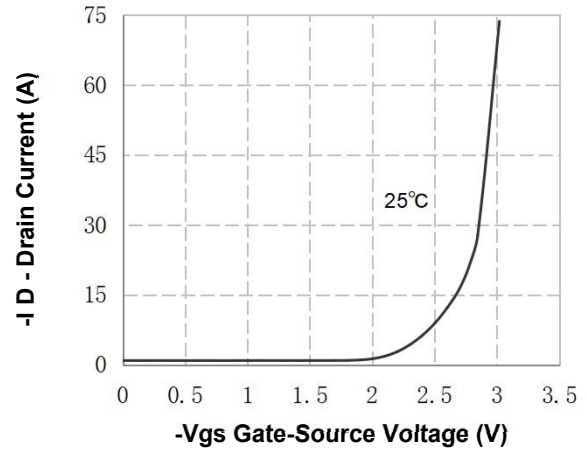


Figure 2. Transfer Characteristics

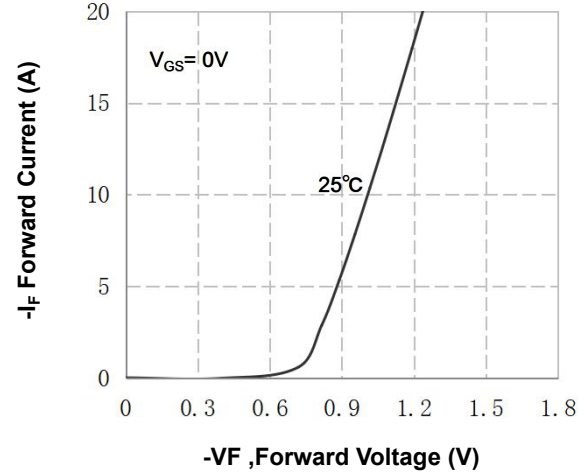


Figure 4. Body Diode Forward Voltage Variation with Source Current and Temperature

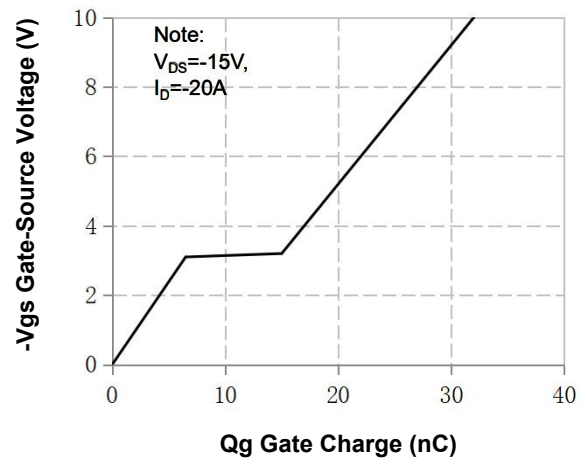


Figure 6. Gate Charge Characteristics

P- Channel Typical Characteristics (Continued)

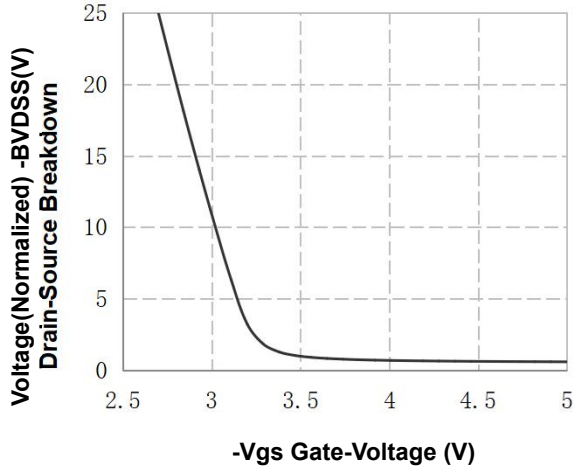


Figure 7. Breakdown Voltage Variation vs Gate-Voltage

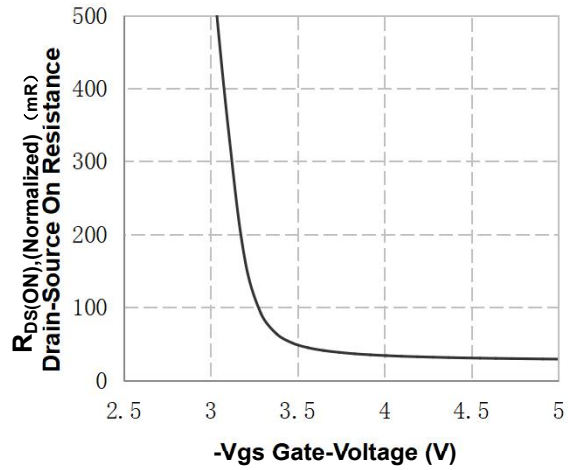


Figure 8. On-Resistance Variation vs Gate Voltage

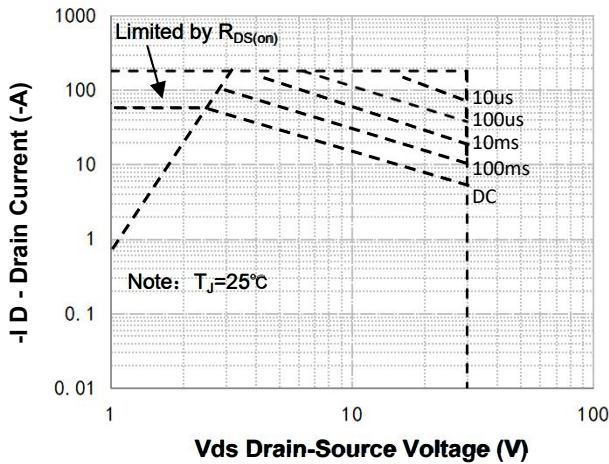


Figure 9. Maximum Safe Operating Area

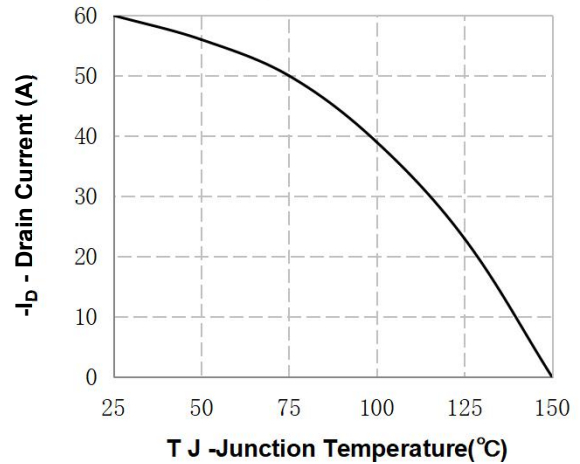


Figure 10. Maximum PContinuous Drain Current vs Case Temperature

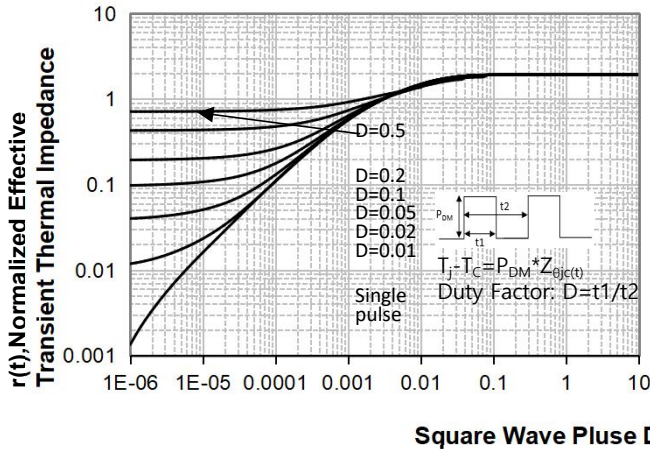
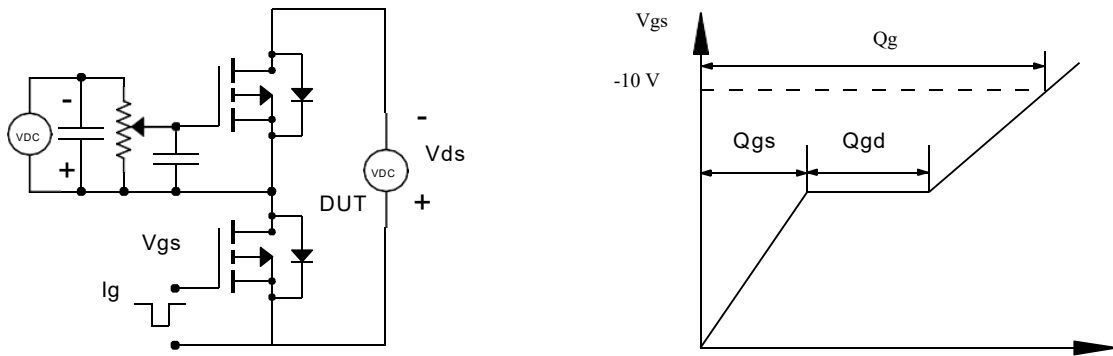
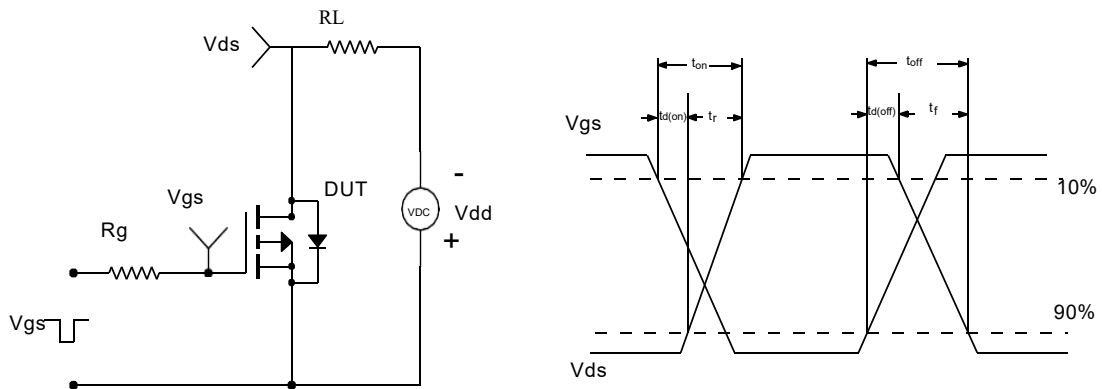


Figure 11. Transient Thermal Response Curve

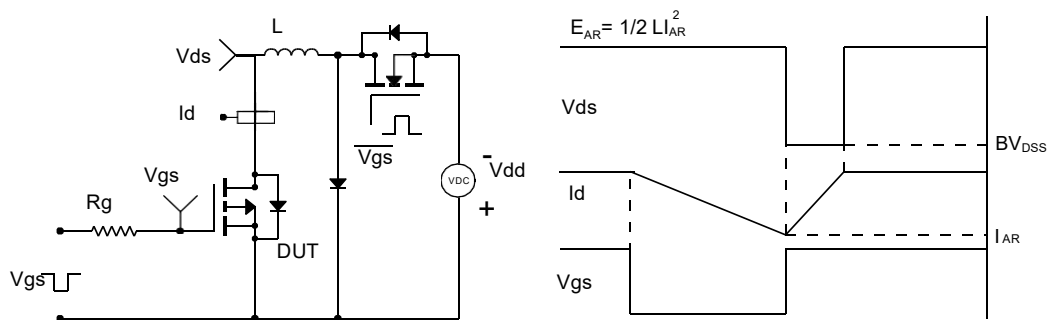
### Gate Charge Test Circuit & Waveform



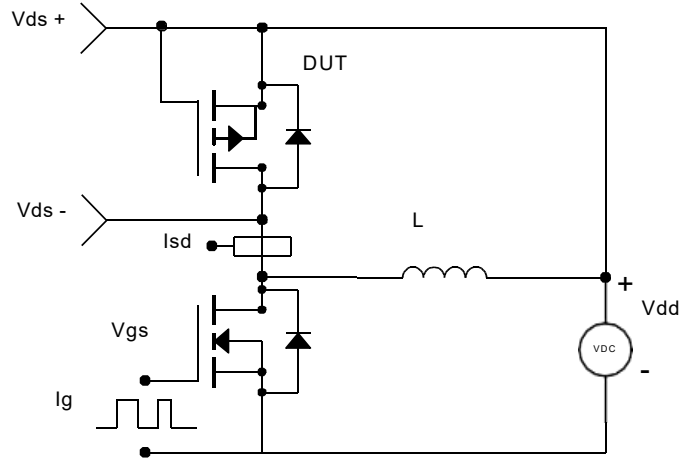
### Resistive Switching Test Circuit & Waveforms



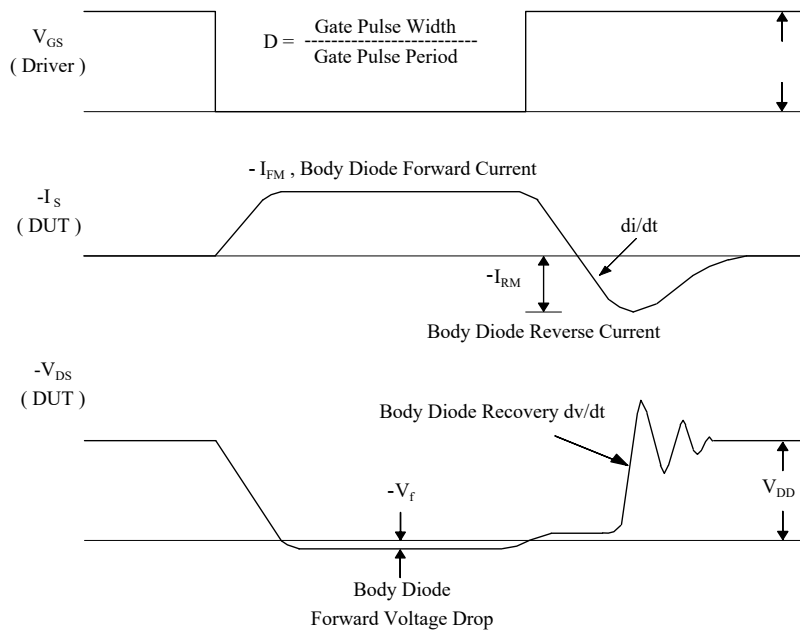
### Unclamped Inductive Switching Test Circuit & Waveforms

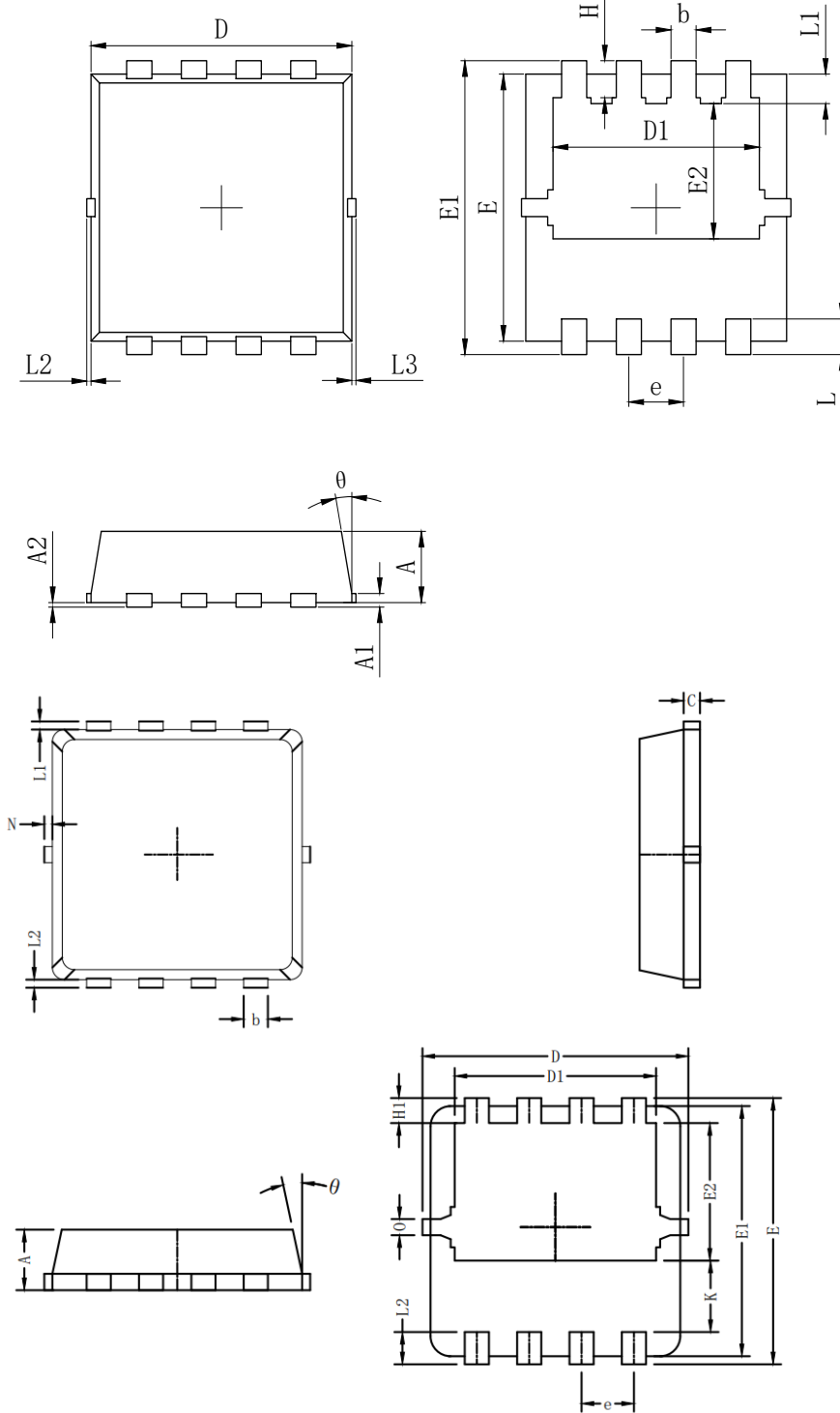


### Peak Diode Recovery dv/dt Test Circuit & Waveforms



- $dv/dt$  controlled by  $R_G$
- $I_{SD}$  controlled by pulse period



**•Dimensions (PDFN3.3×3.3)**


SYMBOL	MILLIMETER		
	MIN	Typ.	MAX
A	0.700	0.800	0.900
A1	0.152 REF.		
A2	0°0.05		
D	3.000	3.100	3.200
D1	2.300	2.450	2.600
E	2.900	3.000	3.100
E1	3.150	3.300	3.450
E2	1.320	1.520	1.720
b	0.200	0.300	0.400
e	0.550	0.650	0.750
L	0.300	0.400	0.500
L1	0.180	0.330	0.480
L2	0°0.100		
L3	0°0.100		
H	0.315	0.415	0.515
θ	8°	10°	12°

Symbols	Millimeters		
	MIN.	NOM.	MAX.
A	0.65	0.75	0.85
b	0.25	0.30	0.35
C	0.15	0.20	0.25
D	3.00	3.10	3.20
D1	2.40	2.50	2.60
E	3.20	3.30	3.40
E1	3.00	3.10	3.20
E2	1.60	1.70	1.80
e	0.65 BSC.		
H1	0.21	0.31	0.41
H2	0.30	0.40	0.50
K	0.78	0.88	0.98
L1/L2	0.10 REF.		
θ	11°	12°	13°
N	0	-	0.15
O	0.2 REF.		


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